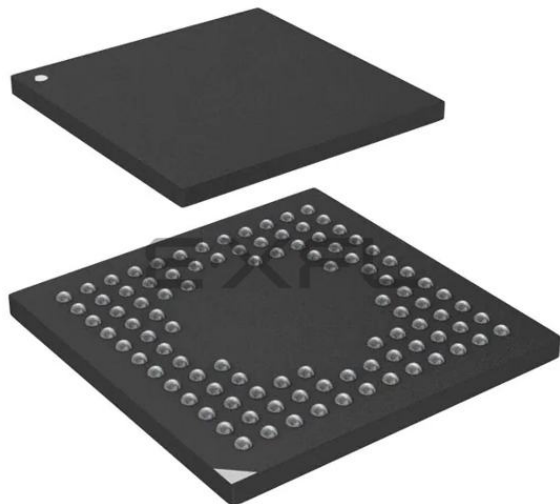




Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	84
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 39x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA
Supplier Device Package	100-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f303veh6tr

Table 49.	EMS characteristics	82
Table 50.	EMI characteristics	83
Table 51.	ESD absolute maximum ratings	83
Table 52.	Electrical sensitivities	84
Table 53.	I/O current injection susceptibility	85
Table 54.	I/O static characteristics	86
Table 55.	Output voltage characteristics	89
Table 56.	I/O AC characteristics	90
Table 57.	NRST pin characteristics	91
Table 58.	TIMx characteristics	92
Table 59.	IWDG min/max timeout period at 40 kHz (LSI)	93
Table 60.	WWDG min-max timeout value @72 MHz (PCLK)	93
Table 61.	I2C timings specification (see I2C specification, rev.03, June 2007)	94
Table 62.	I2C analog filter characteristics	95
Table 63.	SPI characteristics	96
Table 64.	I ² S characteristics	99
Table 65.	USB startup time	101
Table 66.	USB DC electrical characteristics	101
Table 67.	USB: Full-speed electrical characteristics	102
Table 68.	ADC characteristics	103
Table 69.	Maximum ADC RAIN	107
Table 70.	ADC accuracy - limited test conditions, 100-pin packages	108
Table 71.	ADC accuracy, 100-pin packages	110
Table 72.	ADC accuracy - limited test conditions, 64-pin packages	112
Table 73.	ADC accuracy, 64-pin packages	114
Table 74.	ADC accuracy at 1MSPS	115
Table 75.	DAC characteristics	117
Table 76.	Comparator characteristics	119
Table 77.	Operational amplifier characteristics	121
Table 78.	TS characteristics	123
Table 79.	Temperature sensor calibration values	123
Table 80.	V _{BAT} monitoring characteristics	124
Table 81.	LQPF100 – 14 x 14 mm, low-profile quad flat package mechanical data	125
Table 82.	LQFP64 – 10 x 10 mm, low-profile quad flat package mechanical data	128
Table 83.	LQFP48 – 7 x 7 mm, low-profile quad flat package mechanical data	131
Table 84.	WLCSP100 – 100L, 4.166 x 4.628 mm 0.4 mm pitch wafer level chip scale package mechanical data	135
Table 85.	WLCSP100 recommended PCB design rules (0.4 mm pitch)	136
Table 86.	Package thermal characteristics	138
Table 87.	Ordering information scheme	141
Table 88.	Document revision history	142

2 Description

The STM32F303xB/STM32F303xC family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core with FPU operating at a frequency of up to 72 MHz, and embedding a floating point unit (FPU), a memory protection unit (MPU) and an embedded trace macrocell (ETM). The family incorporates high-speed embedded memories (up to 256 Kbytes of Flash memory, up to 40 Kbytes of SRAM) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The devices offer up to four fast 12-bit ADCs (5 Msps), seven comparators, four operational amplifiers, up to two DAC channels, a low-power RTC, up to five general-purpose 16-bit timers, one general-purpose 32-bit timer, and two timers dedicated to motor control. They also feature standard and advanced communication interfaces: up to two I²Cs, up to three SPIs (two SPIs are with multiplexed full-duplex I2Ss), three USARTs, up to two UARTs, CAN and USB. To achieve audio class accuracy, the I2S peripherals can be clocked via an external PLL.

The STM32F303xB/STM32F303xC family operates in the -40 to +85 °C and -40 to +105 °C temperature ranges from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F303xB/STM32F303xC family offers devices in four packages ranging from 48 pins to 100 pins.

The set of included peripherals changes with the device chosen.

3.7.4 Low-power modes

The STM32F303xB/STM32F303xC supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**
In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
- **Stop mode**
Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.
The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the USB wakeup, the RTC alarm, COMPx, I2Cx or U(S)ARTx.
- **Standby mode**
The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.
The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin or an RTC alarm occurs.

Note: The RTC, the IWDG and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.8 Interconnect matrix

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU resources thus power supply consumption. In addition, these hardware connections allow fast and predictable latency.

Table 4. STM32F303xB/STM32F303xC peripheral interconnect matrix

Interconnect source	Interconnect destination	Interconnect action
TIMx	TIMx	Timers synchronization or chaining
	ADCx DAC1	Conversion triggers
	DMA	Memory to memory transfer trigger
	Comp _x	Comparator output blanking
COMPx	TIMx	Timer input: OCREF_CLR input, input capture
ADCx	TIMx	Timer triggered by analog watchdog

3.13.3 V_{BAT} battery voltage monitoring

This embedded hardware feature allows the application to measure the V_{BAT} battery voltage using the internal ADC channel ADC1_IN17. As the V_{BAT} voltage may be higher than V_{DDA} , and thus outside the ADC input range, the V_{BAT} pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the V_{BAT} voltage.

3.13.4 OPAMP reference voltage (VREFOPAMP)

Every OPAMP reference voltage can be measured using a corresponding ADC internal channel: VREFOPAMP1 connected to ADC1 channel 15, VREFOPAMP2 connected to ADC2 channel 17, VREFOPAMP3 connected to ADC3 channel 17, VREFOPAMP4 connected to ADC4 channel 17.

3.14 Digital-to-analog converter (DAC)

Two 12-bit buffered DAC channels can be used to convert digital signals into analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This digital interface supports the following features:

- Two DAC output channels
- 8-bit or 10-bit monotonic output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability (for each channel)
- External triggers for conversion

3.15 Operational amplifier (OPAMP)

The STM32F303xB/STM32F303xC embeds four operational amplifiers with external or internal follower routing and PGA capability (or even amplifier and filter capability with external components). When an operational amplifier is selected, an external ADC channel is used to enable output measurement.

The operational amplifier features:

- 8.2 MHz bandwidth
- 0.5 mA output capability
- Rail-to-rail input/output
- In PGA mode, the gain can be programmed to be 2, 4, 8 or 16.

Table 13. STM32F303xB/STM32F303xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
F6	34	25	-	PC5	I/O	TTa	(1)	USART1_RX, TSC_G3_IO1, EVENTOUT	ADC2_IN11, OPAMP2_VINM, OPAMP1_VINM
J6	35	26	18	PB0	I/O	TTa	-	TIM3_CH3, TIM1_CH2N, TIM8_CH2N, TSC_G3_IO2, EVENTOUT	ADC3_IN12, COMP4_INP, OPAMP3_VINP, OPAMP2_VINP
K6	36	27	19	PB1	I/O	TTa	(4) (5)	TIM3_CH4, TIM1_CH3N, TIM8_CH3N, COMP4_OUT, TSC_G3_IO3, EVENTOUT	ADC3_IN1, OPAMP3_VOUT-
K5	37	28	20	PB2	I/O	TTa	-	TSC_G3_IO4, EVENTOUT	ADC2_IN12, COMP4_INM, OPAMP3_VINM
F8	38	-	-	PE7	I/O	TTa	(1)	TIM1_ETR, EVENTOUT	ADC3_IN13, COMP4_INP
E6	39	-	-	PE8	I/O	TTa	(1)	TIM1_CH1N, EVENTOUT	COMP4_INM, ADC34_IN6
-	40	-	-	PE9	I/O	TTa	(4) (1)	TIM1_CH1, EVENTOUT	ADC3_IN2
-	41	-	-	PE10	I/O	TTa	(1)	TIM1_CH2N, EVENTOUT	ADC3_IN14
H5	42	-	-	PE11	I/O	TTa	(1)	TIM1_CH2, EVENTOUT	ADC3_IN15
G5	43	-	-	PE12	I/O	TTa	(1)	TIM1_CH3N, EVENTOUT	ADC3_IN16
-	44	-	-	PE13	I/O	TTa	(1)	TIM1_CH3, EVENTOUT	ADC3_IN3
-	45	-	-	PE14	I/O	TTa	(4) (1)	TIM1_CH4, TIM1_BKIN2, EVENTOUT	ADC4_IN1
-	46	-	-	PE15	I/O	TTa	(4) (1)	USART3_RX, TIM1_BKIN, EVENTOUT	ADC4_IN2
K4	47	29	21	PB10	I/O	TTa	-	USART3_TX, TIM2_CH3, TSC_SYNC, EVENTOUT	COMP5_INM, OPAMP4_VINM, OPAMP3_VINM
K3	48	30	22	PB11	I/O	TTa	-	USART3_RX, TIM2_CH4, TSC_G6_IO1, EVENTOUT	COMP6_INP, OPAMP4_VINP
K1, J1, K2	49	31	23	VSS	S	-	-	Digital ground	
J5	50	32	24	VDD	S	-	-	Digital power supply	
J4	51	33	25	PB12	I/O	TTa	(4) (5)	SPI2_NSS, I2S2_WS, I2C2_SMB, USART3_CK, TIM1_BKIN, TSC_G6_IO2, EVENTOUT	ADC4_IN3, COMP3_INM, OPAMP4_VOUT

Table 17. Alternate functions for port D

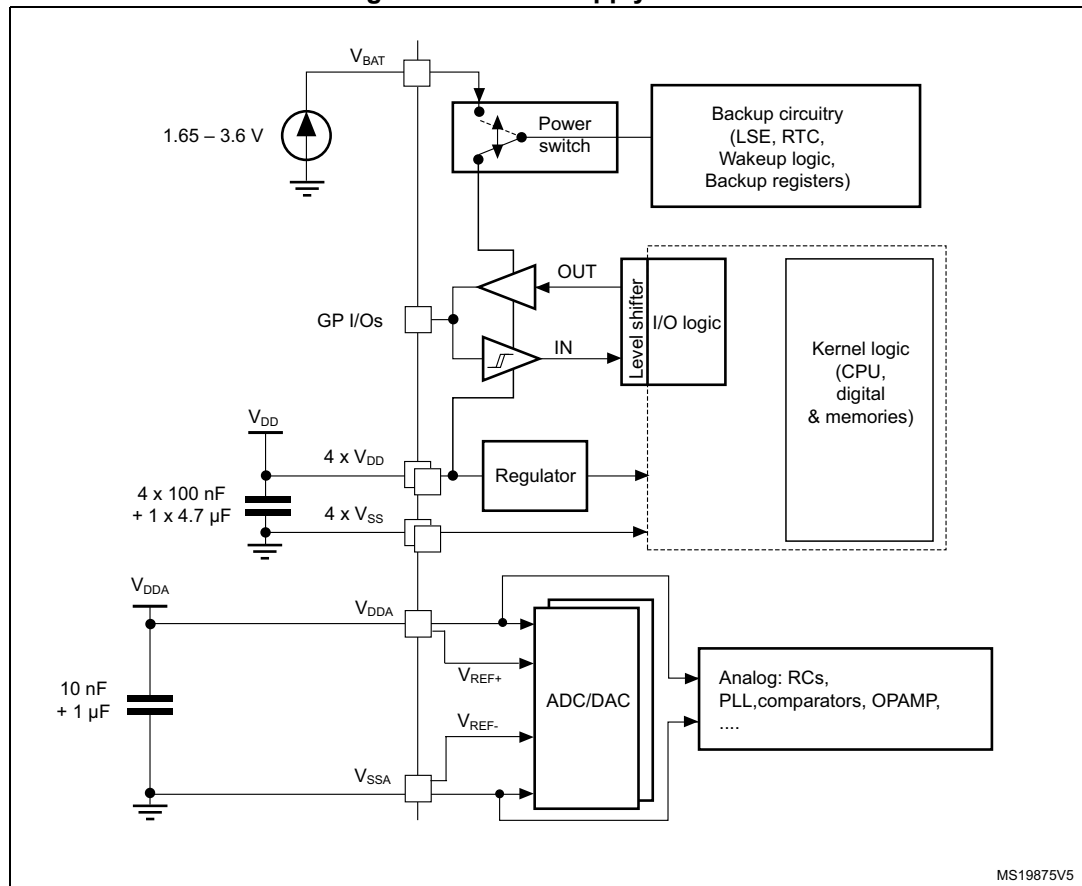
Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PD0	EVENTOUT	-	-	-	-	-	CAN_RX
PD1	EVENTOUT	-	-	TIM8_CH4	-	TIM8_BKIN2	CAN_TX
PD2	EVENTOUT	TIM3_ETR	-	TIM8_BKIN	UART5_RX	-	-
PD3	EVENTOUT	TIM2_CH1_ETR	-	-	-	-	USART2_CTS
PD4	EVENTOUT	TIM2_CH2	-	-	-	-	USART2_RTS_DE
PD5	EVENTOUT	-	-	-	-	-	USART2_TX
PD6	EVENTOUT	TIM2_CH4	-	-	-	-	USART2_RX
PD7	EVENTOUT	TIM2_CH3	-	-	-	-	USART2_CK
PD8	EVENTOUT	-	-	-	-	-	USART3_TX
PD9	EVENTOUT	-	-	-	-	-	USART3_RX
PD10	EVENTOUT	-	-	-	-	-	USART3_CK
PD11	EVENTOUT	-	-	-	-	-	USART3_CTS
PD12	EVENTOUT	TIM4_CH1	TSC_G8_IO1	-	-	-	USART3_RTS_DE
PD13	EVENTOUT	TIM4_CH2	TSC_G8_IO2	-	-	-	-
PD14	EVENTOUT	TIM4_CH3	TSC_G8_IO3	-	-	-	-
PD15	EVENTOUT	TIM4_CH4	TSC_G8_IO4	-	-	SPI2_NSS	-

Table 20. STM32F303xB/STM32F303xC memory map, peripheral register boundary addresses (continued)

Bus	Boundary address	Size (bytes)	Peripheral
	0x4000 8000 - 0x4000 FFFF	32 K	Reserved
APB1	0x4000 7800 - 0x4000 7FFF	2 K	Reserved
	0x4000 7400 - 0x4000 77FF	1 K	DAC (dual)
	0x4000 7000 - 0x4000 73FF	1 K	PWR
	0x4000 6800 - 0x4000 6FFF	2 K	Reserved
	0x4000 6400 - 0x4000 67FF	1 K	bxCAN
	0x4000 6000 - 0x4000 63FF	1 K	USB SRAM 512 bytes
	0x4000 5C00 - 0x4000 5FFF	1 K	USB device FS
	0x4000 5800 - 0x4000 5BFF	1 K	I2C2
	0x4000 5400 - 0x4000 57FF	1 K	I2C1
	0x4000 5000 - 0x4000 53FF	1 K	UART5
	0x4000 4C00 - 0x4000 4FFF	1 K	UART4
	0x4000 4800 - 0x4000 4BFF	1 K	USART3
	0x4000 4400 - 0x4000 47FF	1 K	USART2
	0x4000 4000 - 0x4000 43FF	1 K	I2S3ext
	0x4000 3C00 - 0x4000 3FFF	1 K	SPI3/I2S3
	0x4000 3800 - 0x4000 3BFF	1 K	SPI2/I2S2
	0x4000 3400 - 0x4000 37FF	1 K	I2S2ext
	0x4000 3000 - 0x4000 33FF	1 K	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 K	WWDG
	0x4000 2800 - 0x4000 2BFF	1 K	RTC
	0x4000 1800 - 0x4000 27FF	4 K	Reserved
	0x4000 1400 - 0x4000 17FF	1 K	TIM7
	0x4000 1000 - 0x4000 13FF	1 K	TIM6
	0x4000 0C00 - 0x4000 0FFF	1 K	Reserved
	0x4000 0800 - 0x4000 0BFF	1 K	TIM4
	0x4000 0400 - 0x4000 07FF	1 K	TIM3
	0x4000 0000 - 0x4000 03FF	1 K	TIM2

6.1.6 Power supply scheme

Figure 11. Power supply scheme



1. Dotted lines represent the internal connections on low pin count packages, joining the dedicated supply pins.

Caution: Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} etc..) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

2. V_{REF+} must be always lower or equal than V_{DDA} ($V_{REF+} \leq V_{DDA}$). If unused then it must be connected to V_{DDA} .
3. V_{IN} maximum must always be respected. Refer to [Table 22: Current characteristics](#) for the maximum allowed injected current values.
4. Include VREF- pin.

Table 22. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD} power lines (source)	160	mA
ΣI_{VSS}	Total current out of sum of all V_{SS} ground lines (sink)	-160	
I_{VDD}	Maximum current into each V_{DD} power line (source) ⁽¹⁾	100	
I_{VSS}	Maximum current out of each V_{SS} ground line (sink) ⁽¹⁾	-100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin	25	
	Output current source by any I/O and control pin	-25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins ⁽²⁾	80	
	Total output current sourced by sum of all IOs and control pins ⁽²⁾	-80	
$I_{INJ(PIN)}$	Injected current on FT, FTf and B pins ⁽³⁾	-5/+0	
	Injected current on TC and RST pin ⁽⁴⁾	± 5	
	Injected current on TTa pins ⁽⁵⁾	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins) ⁽⁶⁾	± 25	

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} and V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 21: Voltage characteristics](#) for the maximum allowed input voltage values.
5. A positive injection is induced by $V_{IN} > V_{DDA}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer also to [Table 21: Voltage characteristics](#) for the maximum allowed input voltage values. Negative injection disturbs the analog performance of the device. See note ⁽²⁾ below [Table 70](#).
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 23. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 32. Typical and maximum V_{DD} consumption in Stop and Standby modes

Symbol	Parameter	Conditions	Typ @ V_{DD} ($V_{DD}=V_{DDA}$)						Max ⁽¹⁾			Unit
			2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	$T_A = 25\text{ °C}$	$T_A = 85\text{ °C}$	$T_A = 105\text{ °C}$	
I_{DD}	Supply current in Stop mode	Regulator in run mode, all oscillators OFF	20.05	20.33	20.42	20.50	20.67	20.80	44.2 ⁽²⁾	350	735 ⁽²⁾	μA
		Regulator in low-power mode, all oscillators OFF	7.63	7.77	7.90	8.07	8.17	8.33	30.6 ⁽²⁾	335	720 ⁽²⁾	
	Supply current in Standby mode	LSI ON and IWDG ON	0.80	0.96	1.09	1.23	1.37	1.51	-	-	-	
		LSI OFF and IWDG OFF	0.60	0.74	0.83	0.93	1.02	1.11	5.0 ⁽²⁾	7.8	13.3 ⁽²⁾	

1. Guaranteed by characterization results unless otherwise specified.

2. Data based on characterization results and tested in production.

Table 33. Typical and maximum V_{DDA} consumption in Stop and Standby modes

Symbol	Parameter	Conditions		Typ @V _{DD} (V _{DD} = V _{DDA})						Max ⁽¹⁾			Unit
				2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DDA}	Supply current in Stop mode	V _{DDA} monitoring ON	Regulator in run mode, all oscillators OFF	1.81	1.95	2.07	2.20	2.35	2.52	3.7	5.5	8.8	μA
			Regulator in low-power mode, all oscillators OFF	1.81	1.95	2.07	2.20	2.35	2.52	3.7	5.5	8.8	
	Supply current in Standby mode	V _{DDA} monitoring ON	LSI ON and IWDG ON	2.22	2.42	2.59	2.78	3.0	3.24	-	-	-	
			LSI OFF and IWDG OFF	1.69	1.82	1.94	2.08	2.23	2.40	3.5	5.4	9.2	
	Supply current in Stop mode	V _{DDA} monitoring OFF	Regulator in run mode, all oscillators OFF	1.05	1.08	1.10	1.15	1.22	1.29	-	-	-	
			Regulator in low-power mode, all oscillators OFF	1.05	1.08	1.10	1.15	1.22	1.29	-	-	-	
	Supply current in Standby mode	V _{DDA} monitoring OFF	LSI ON and IWDG ON	1.44	1.52	1.60	1.71	1.84	1.98	-	-	-	
			LSI OFF and IWDG OFF	0.93	0.95	0.98	1.02	1.08	1.15	-	-	-	

1. Guaranteed by characterization results.

The total consumption is the sum of I_{DD} and I_{DDA} .

Low-speed external user clock generated from an external source

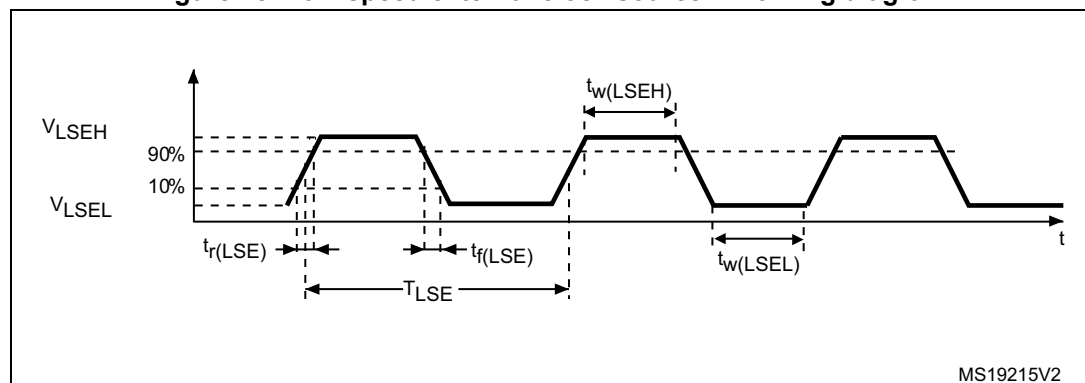
In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in [Section 6.3.14](#). However, the recommended clock input waveform is shown in [Figure 15](#)

Table 41. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency ⁽¹⁾	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	

1. Guaranteed by design.

Figure 15. Low-speed external clock source AC timing diagram



6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 49](#). They are based on the EMS levels and classes defined in the application note AN1709.

Table 49. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, $T_A = +25^\circ\text{C}$, $f_{HCLK} = 72\text{ MHz}$ conforms to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP100, $T_A = +25^\circ\text{C}$, $f_{HCLK} = 72\text{ MHz}$ conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

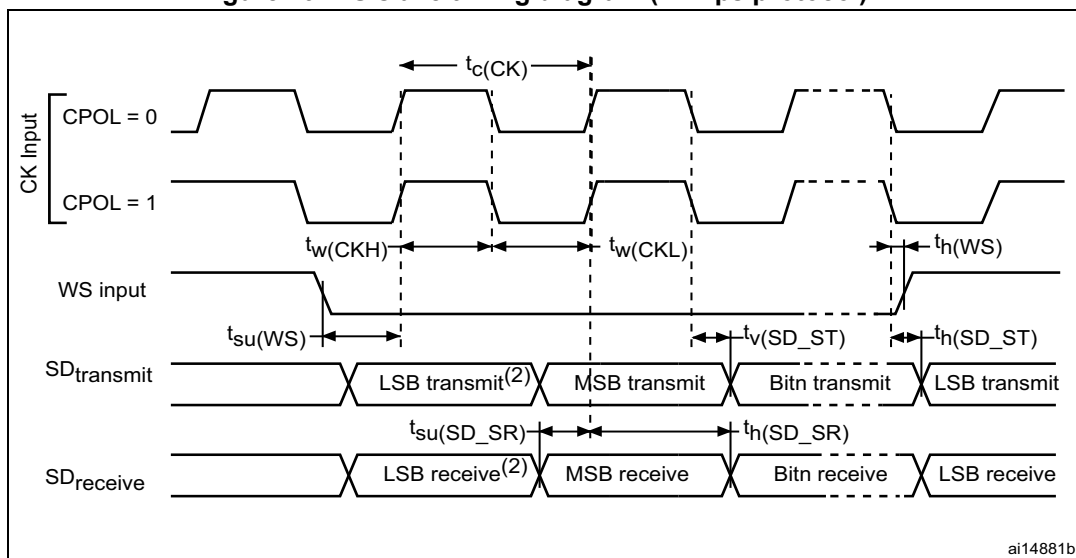
EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

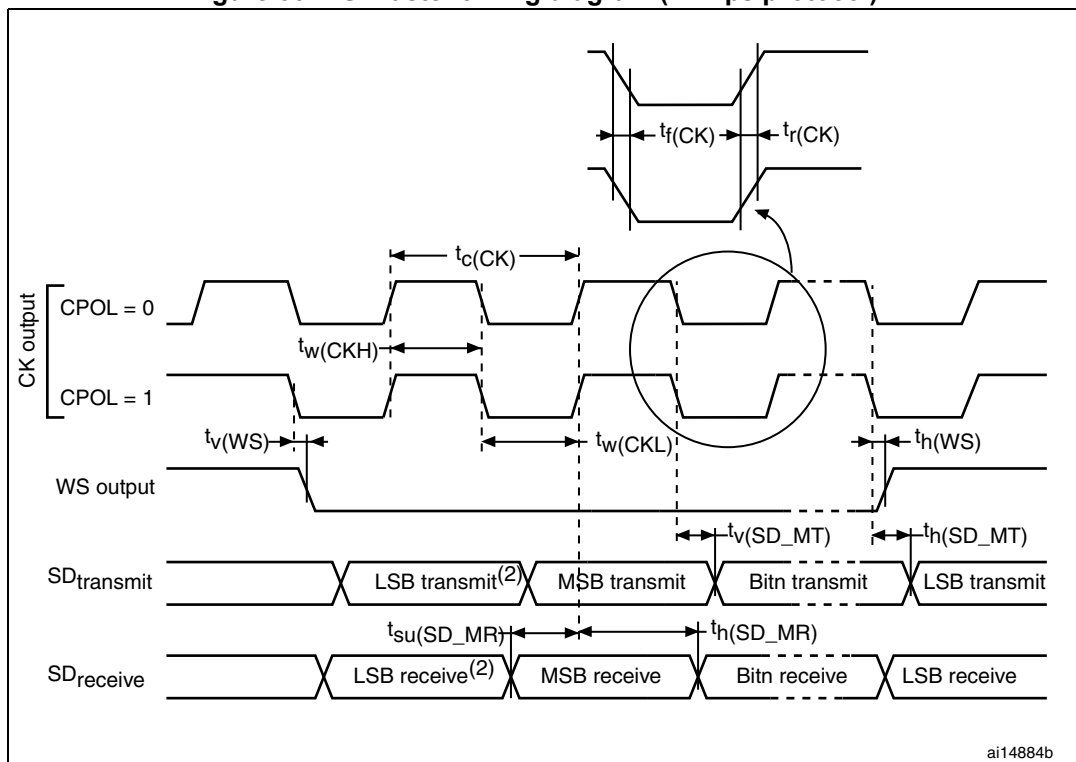
Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Figure 29. I²S slave timing diagram (Philips protocol)⁽¹⁾

1. Measurement points are done at $0.5V_{DD}$ and with external $C_L=30$ pF.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 30. I²S master timing diagram (Philips protocol)⁽¹⁾

1. Measurement points are done at $0.5V_{DD}$ and with external $C_L=30$ pF.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Table 68. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_S^{(1)}$	Sampling time	$f_{ADC} = 72 \text{ MHz}$	0.021	-	8.35	μs
		-	1.5	-	601.5	$1/f_{ADC}$
$T_{ADCVREG_STUP}^{(1)}$	ADC Voltage Regulator Start-up time	-	-	-	10	μs
$t_{CONV}^{(1)}$	Total conversion time (including sampling time)	$f_{ADC} = 72 \text{ MHz}$ Resolution = 12 bits	0.19	-	8.52	μs
		Resolution = 12 bits	14 to 614 (t_S for sampling + 12.5 for successive approximation)			$1/f_{ADC}$
$CMIR^{(1)}$	Common Mode Input signal Range	ADC differential mode	$(V_{SSA}+V_{REF+})/2$ -10%	$(V_{SSA}+V_{REF+})/2$	$(V_{SSA}+V_{REF+})/2$ + 10%	V

1. Data guaranteed by design.

2. V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA} , depending on the package. Refer to [Section 4: Pinouts and pin description](#) for further details.

Table 69. Maximum ADC R_{AIN} ⁽¹⁾

Resolution	Sampling cycle @ 72 MHz	Sampling time [ns] @ 72 MHz	R_{AIN} max (k Ω)		
			Fast channels ⁽²⁾	Slow channels	Other channels ⁽³⁾
12 bits	1.5	20.83	0.018	NA	NA
	2.5	34.72	0.150	NA	0.022
	4.5	62.50	0.470	0.220	0.180
	7.5	104.17	0.820	0.560	0.470
	19.5	270.83	2.70	1.80	1.50
	61.5	854.17	8.20	6.80	4.70
	181.5	2520.83	22.0	18.0	15.0
	601.5	8354.17	82.0	68.0	47.0
10 bits	1.5	20.83	0.082	NA	NA
	2.5	34.72	0.270	0.082	0.100
	4.5	62.50	0.560	0.390	0.330
	7.5	104.17	1.20	0.82	0.68
	19.5	270.83	3.30	2.70	2.20
	61.5	854.17	10.0	8.2	6.8
	181.5	2520.83	33.0	27.0	22.0
	601.5	8354.17	100.0	82.0	68.0
8 bits	1.5	20.83	0.150	NA	0.039
	2.5	34.72	0.390	0.180	0.180
	4.5	62.50	0.820	0.560	0.470
	7.5	104.17	1.50	1.20	1.00
	19.5	270.83	3.90	3.30	2.70
	61.5	854.17	12.00	12.00	8.20
	181.5	2520.83	39.00	33.00	27.00
	601.5	8354.17	100.00	100.00	82.00
6 bits	1.5	20.83	0.270	0.100	0.150
	2.5	34.72	0.560	0.390	0.330
	4.5	62.50	1.200	0.820	0.820
	7.5	104.17	2.20	1.80	1.50
	19.5	270.83	5.60	4.70	3.90
	61.5	854.17	18.0	15.0	12.0
	181.5	2520.83	56.0	47.0	39.0
	601.5	8354.17	100.00	100.0	100.0

1. Guaranteed by characterization results.

2. All fast channels, expect channels on PA2, PA6, PB1, PB12.

Table 73. ADC accuracy, 64-pin packages⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions			Min ⁽⁴⁾	Max ⁽⁴⁾	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz, Sampling freq. ≤ 5 Msps 2.0 V ≤ V _{DDA} ≤ 3.6 V 64-pin package	Single ended	Fast channel 5.1 Ms	-	±6.5	LSB
				Slow channel 4.8 Ms	-	±6.5	
			Differential	Fast channel 5.1 Ms	-	±4	
				Slow channel 4.8 Ms	-	±4.5	
EO	Offset error		Single ended	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2.5	
				Slow channel 4.8 Ms	-	±2.5	
EG	Gain error		Single ended	Fast channel 5.1 Ms	-	±6	
				Slow channel 4.8 Ms	-	±6	
			Differential	Fast channel 5.1 Ms	-	±3.5	
				Slow channel 4.8 Ms	-	±4	
ED	Differential linearity error		Single ended	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
			Differential	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
EL	Integral linearity error	Single ended	Fast channel 5.1 Ms	-	±3		
			Slow channel 4.8 Ms	-	±3.5		
		Differential	Fast channel 5.1 Ms	-	±2		
			Slow channel 4.8 Ms	-	±2.5		
ENOB ⁽⁵⁾	Effective number of bits	Single ended	Fast channel 5.1 Ms	10.4	-	bits	
			Slow channel 4.8 Ms	10.4	-		
		Differential	Fast channel 5.1 Ms	10.8	-		
			Slow channel 4.8 Ms	10.8	-		
SINAD ⁽⁵⁾	Signal-to-noise and distortion ratio	Single ended	Fast channel 5.1 Ms	64	-	dB	
			Slow channel 4.8 Ms	63	-		
		Differential	Fast channel 5.1 Ms	67	-		
			Slow channel 4.8 Ms	67	-		

6.3.19 DAC electrical specifications

Table 75. DAC characteristics

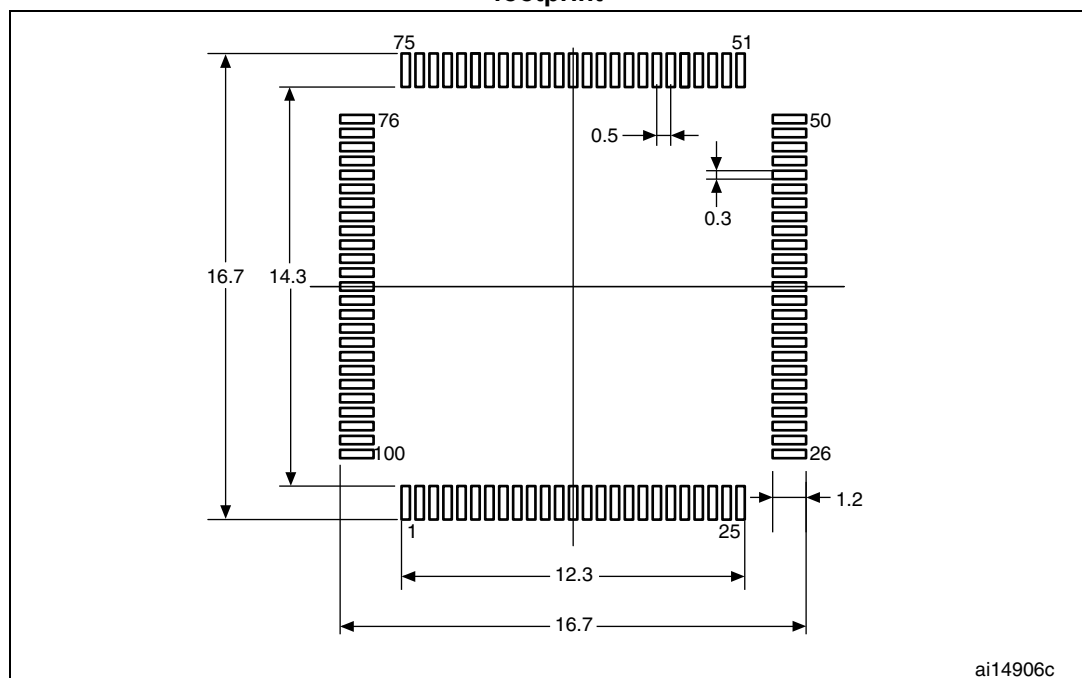
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-	2.4	-	3.6	V
$R_{LOAD}^{(1)}$	Resistive load	DAC output buffer ON Connected to V_{SSA}	5	-	-	k Ω
		Connected to V_{DDA}	25	-	-	
$R_O^{(1)}$	Output impedance	DAC output buffer OFF	-	-	15	k Ω
$C_{LOAD}^{(1)}$	Capacitive load	DAC output buffer ON	-	-	50	pF
$V_{DAC_OUT}^{(1)}$	Voltage on DAC_OUT output	Corresponds to 12-bit input code (0x0E0) to (0xF1C) at $V_{DDA} = 3.6$ V and (0x155) and (0xEAB) at $V_{DDA} = 2.4$ V DAC output buffer ON.	0.2	-	$V_{DDA} - 0.2$	V
		DAC output buffer OFF	-	0.5	$V_{DDA} - 1\text{LSB}$	mV
$I_{DDA}^{(3)}$	DAC DC current consumption in quiescent mode (Standby mode) ⁽²⁾	With no load, middle code (0x800) on the input.	-	-	380	μ A
		With no load, worst code (0xF1C) on the input.	-	-	480	μ A
DNL ⁽³⁾	Differential non linearity Difference between two consecutive code-1LSB)	Given for a 10-bit input code	-	-	± 0.5	LSB
		Given for a 12-bit input code	-	-	± 2	LSB
INL ⁽³⁾	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095)	Given for a 10-bit input code	-	-	± 1	LSB
		Given for a 12-bit input code	-	-	± 4	LSB
Offset ⁽³⁾	Offset error (difference between measured value at Code (0x800) and the ideal value = $V_{DDA}/2$)	-	-	-	± 10	mV
		Given for a 10-bit input code at $V_{DDA} = 3.6$ V	-	-	± 3	LSB
		Given for a 12-bit input code at $V_{DDA} = 3.6$ V	-	-	± 12	LSB
Gain error ⁽³⁾	Gain error	Given for a 12-bit input code	-	-	± 0.5	%
$t_{SETTLING}^{(3)}$	Settling time (full scale: for a 12-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value $\pm 1\text{LSB}$)	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ k Ω	-	3	4	μ s
Update rate ⁽³⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ k Ω	-	-	1	MS/s

Table 81. LQPF100 – 14 x 14 mm, low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
c	0.09	-	0.2	0.0035	-	0.0079
D	15.80	16.00	16.2	0.622	0.6299	0.6378
D1	13.80	14.00	14.2	0.5433	0.5512	0.5591
D3	-	12.00	-	-	0.4724	-
E	15.80	16.00	16.2	0.622	0.6299	0.6378
E1	13.80	14.00	14.2	0.5433	0.5512	0.5591
E3	-	12.00	-	-	0.4724	-
e	-	0.50	-	-	0.0197	-
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.08	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 40. LQFP100 – 14 x 14 mm, low-profile quad flat package recommended footprint



1. Dimensions are in millimeters.

7.5.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in [Section 8: Ordering information](#).

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F303xB/STM32F303xC at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature $T_{Amax} = 82\text{ °C}$ (measured according to JESD51-2),
 $I_{DDmax} = 50\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 3 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$ and maximum 2 I/Os used at the same time in output at low level with $I_{OL} = 20\text{ mA}$, $V_{OL} = 1.3\text{ V}$

$$P_{INTmax} = 50\text{ mA} \times 3.5\text{ V} = 175\text{ mW}$$

$$P_{IOmax} = 3 \times 8\text{ mA} \times 0.4\text{ V} + 2 \times 20\text{ mA} \times 1.3\text{ V} = 61.6\text{ mW}$$

This gives: $P_{INTmax} = 175\text{ mW}$ and $P_{IOmax} = 61.6\text{ mW}$:

$$P_{Dmax} = 175 + 61.6 = 236.6\text{ mW}$$

Thus: $P_{Dmax} = 236.6\text{ mW}$

Using the values obtained in [Table 86](#) T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

$$T_{Jmax} = 82\text{ °C} + (45\text{ °C/W} \times 236.6\text{ mW}) = 82\text{ °C} + 10.65\text{ °C} = 92.65\text{ °C}$$

This is within the range of the suffix 6 version parts ($-40 < T_J < 105\text{ °C}$).

In this case, parts must be ordered at least with the temperature range suffix 6 (see [Section 8: Ordering information](#)).

8 Ordering information

Table 87. Ordering information scheme

Example:	STM32	F	303	R	B	T	6	xxx
Device family STM32 = ARM-based 32-bit microcontroller								
Product type F = general-purpose								
Device subfamily 303 = STM32F303xx								
Pin count C = 48 pins R = 64 pins V = 100 pins								
Flash memory size B = 128 Kbytes of Flash memory C = 256 Kbytes of Flash memory								
Package T = LQFP Y = WLCSP								
Temperature range 6 = Industrial temperature range, –40 to 85 °C 7 = Industrial temperature range, –40 to 105 °C								
Options xxx = programmed parts TR = tape and reel								

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.